Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
Tech ID: 23656 / UC Case 2008-415-0

BRIEF DESCRIPTION

A novel approach to reducing or possibly eliminating the polarization effects in GaN-based optoelectronic devices.

BACKGROUND

Conventional nitride technology for electronic and optoelectronic devices employs nitride films grown along the polar c-direction. However, conventional structures in III-nitride based optoelectronic and electronic devices suffer from the undesirable quantum-confined Stark effect (QCSE), due to the existence of strong piezoelectric and spontaneous polarizations. One approach to eliminating the polarization effects in devices is to grow the devices on nonpolar planes of the crystal. Unfortunately, growth on nonpolar nitrides remains challenging and has not yet been widely adopted in the III-nitride industry.

DESCRIPTION

Researchers at the University of California, Santa Barbara have developed a novel approach to reducing or possibly eliminating the polarization effects in GaN-based optoelectronic devices. This approach includes growing the devices on semipolar planes of the crystal. Using semipolar planes instead of c-plane nitrides will reduce total polarization, and there may even be zero polarization for specific alloy compositions. Reducing the polarization field allows for the growth of thicker quantum wells. With thicker quantum wells, higher Indium composition and thus longer wavelength emission can be achieved. The novel approach allows for the fabrication of blue, green, and yellow LEDs on semipolar (Al, In, Ga, B)N semiconductor crystals.

ADVANTAGES

- Growth of thicker quantum wells
- Reduced polarization fields in the device structure
- Reduced defect formation in the active layer

INVENTORS

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OTHER INFORMATION

KEYWORDS
indssl, indLED, green LED, blue LED, infeat

CATEGORIZED AS
- Engineering
- Energy
- Lighting
- Other
- Semiconductors
- Design and Fabrication

RELATED CASES
2008-415-0
Longer wavelength emission

APPLICATIONS

- Green, yellow, and blue GaN based light emitting diodes
- Laser diodes
- Multi-junction solar cells

PATENT STATUS

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ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
- Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- III-Nitride-Based Vertical Cavity Surface Emitting Laser (VCSEL) with a Dielectric P-Side Lens
- Aluminum-cladding-free Nonpolar III-Nitride LEDs and LDs
- Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
- Defect Reduction in GaN films using in-situ SiNx Nanomask
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Implantable Light Irradiation Device For Photodynamic Therapy
- Low Temperature Deposition of Magnesium Doped Nitride Films
- Transparent Mirrorless (TML) LEDs
- Improved GaN Substrates Prepared with Ammonothermal Growth
- Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- Method for Enhancing Growth of Semipolar Nitride Devices
- Ultraviolet Laser Diode on Nano-Porous AlGaN template
- Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
- Nonpolar III-Nitride LEDs With Long Wavelength Emission
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- Method for Growing High-Quality Group III-Nitride Crystals
- Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure
- Oxyfluoride Phosphors for Use in White Light LEDs
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Group III-N Light Emitting Devices Enhanced By Stress From Post-Growth Deposited Films
- Thermally Stable, Laser-Driven White Lighting Device
MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
Methods for Fabricating III-Nitride Tunnel Junction Devices
Low-Droop LED Structure on GaN Semi-polar Substrates
Contact Architectures for Tunnel Junction Devices
Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material
Growth of Semipolar III-V Nitride Films with Lower Defect Density
III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
Tunable White Light Based on Polarization-Sensitive LEDs
Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
Growth of High-Performance M-plane GaN Optical Devices
Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
Improved Anisotropic Strain Control in Semipolar Nitride Devices
Novel Multi-layer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
III-V Nitride Device Structures on Patterned Substrates
Method for Increasing GaN Substrate Area in Nitride Devices
High-Intensity Solid State White Laser Diode
Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
GaN-Based Thermoelectric Device for Micro-Power Generation
Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
LED Device Structures with Minimized Light Re-Absorption
Growth of Planar Semi-Polar Gallium Nitride
High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys
Defect Reduction of Non-Polar and Semi-Polar III-Nitrides
III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture
Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD